

Attorney Docket No. 0756-2131

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:) Group Art Unit: 2811
Shunpei YAMAZAKI et al.) Examiner: S. Crane
Serial No. 09/535,015)
Filed: March 24, 2000)
For: METHOD OF MANUFACTURING A)
SEMICONDUCTOR DEVICE)
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Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing information known to Applicant and requests that this information be made of record in the above identified application. Copies are submitted herewith in accordance with 37 C.F.R. 1.98(a).

A check in the amount of \$180 is being submitted to comply with the provisions of 37 C.F.R. § 1.97(c).

Respectfully submitted,


Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
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(571) 434-6789

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Sheet

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of

1

Complete if Known

Application Number	09/535,015
Filing Date	March 24, 2000
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2811
Examiner Name	S. Crane

Attorney Docket Number

0756-2131

U.S. PATENT DOCUMENTS

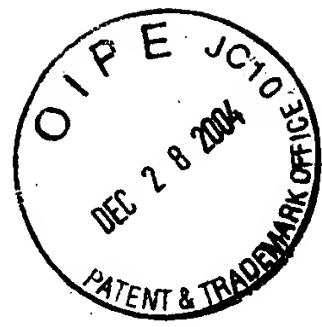
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		5,531,862		Otsubo et al.	07/02/1996	
		5,575,883		Nishikawa	11/19/1996	
		5,704,986		Chen et al.	01/06/1998	
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		6,294,441		Yamazaki	09/25/2001	
		6,461,943		Yamazaki et al.	10/08/2002	
		6,465,287		Yamazaki et al.	10/15/2002	
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		6,528,358		Yamazaki et al.	03/04/2003	
		6,620,711		Yamazaki	09/16/2003	

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Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		JP	08-045839			02/16/1996		Abst.
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		JP	08-097169			04/12/1996		Abst.

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2. Form PTO-1449

in re PATENT application of:

Shunpei YAMAZAKI et al.

Serial No. 09/535,015

Filed: 03/24/2000

Title: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

Due date: 09/15/2000



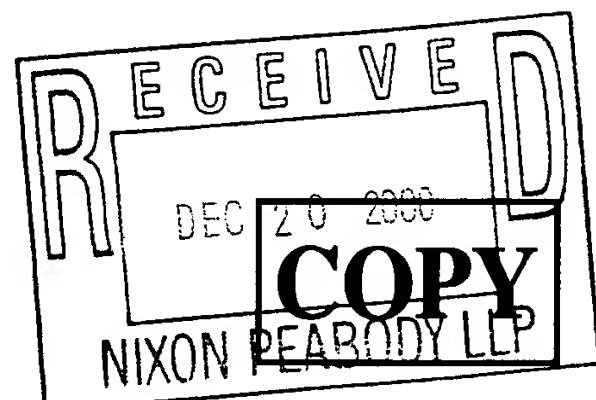
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In re PATENT application of:)
Shunpei YAMAZAKI et al.) Art Unit: 2825
Serial No. 09/535,015) Examiner: Unassigned
Filed: 03/24/2000)
For: METHOD OF MANUFACTURING A)
SEMICONDUCTOR DEVICE)

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference(s) listed on the attached Form PTO-1449 be made of record in the above-identified application. Copies of the references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The following two articles were cited by the Examiner in the following Applications:

Kuo, "Thin Film Transistor Technologies", Vol. 94-35, PP. 116-122, The Electrochemical Society Proceedings, cited in Serial No's 08/784,292 and 09/233,450.

"Thermo Auto-Chrome Full Color Recording Technology", May 31, 1995, Technology Information Association, Patent No. 6,093,934, Serial No. 08/785,536.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 19-2380. A duplicate copy of this sheet is attached.

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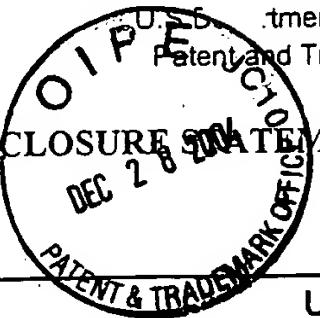
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Filing Date: March 24, 2000

Group Art Unit: 2825

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	5,580,815	12/03/1996	Hsu et al.			
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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	01-187814	07/27/1989	Japan			Full
	01-187874	07/27/1989	Japan			Abst.
	01-187875	07/27/1989	Japan			Abst.
	01-206632	08/18/1989	Japan			Abst.
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	02-275641	11/09/1990	Japan			Abst.
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	05-082442	04/02/1993	Japan			Abst.
	05-107561	04/30/1993	Japan			Abst.
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	08-129358	05/21/1996	Japan			Abst.
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	08-129360	05/21/1996	Japan			Abst.	
	08-234683	09/13/1996	Japan			Abst.	
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